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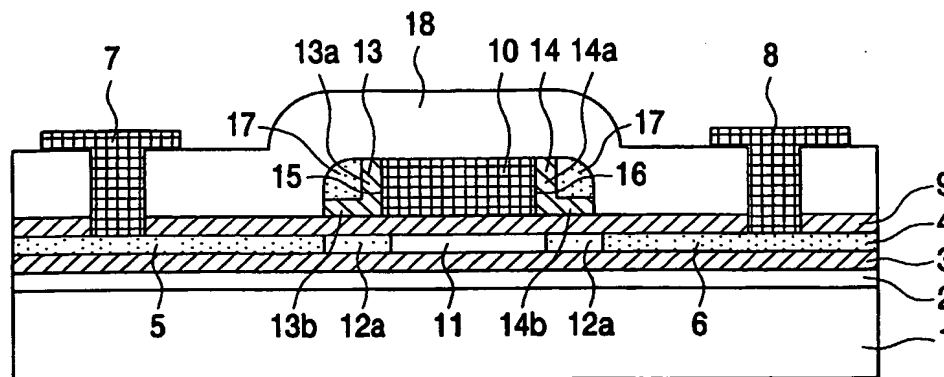
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(54) Title: **THIN FILM TRANSISTORS AND METHODS OF MANUFACTURE THEREOF**



(57) Abstract: A polycrystalline silicon GOLDD TFT with a gate (10) overlying its channel (11) is fabricated by using the gate (10) as a mask during a first dopant implantation step. Spacers (13, 14) are then formed adjacent to the gate (10), which comprise portions of a thin metallic layer (19) which are defined by fillets (17) in an etching process. The spacers and gate are then used as a mask for doping source and drain regions, thereby providing a self-aligned fabrication technique.